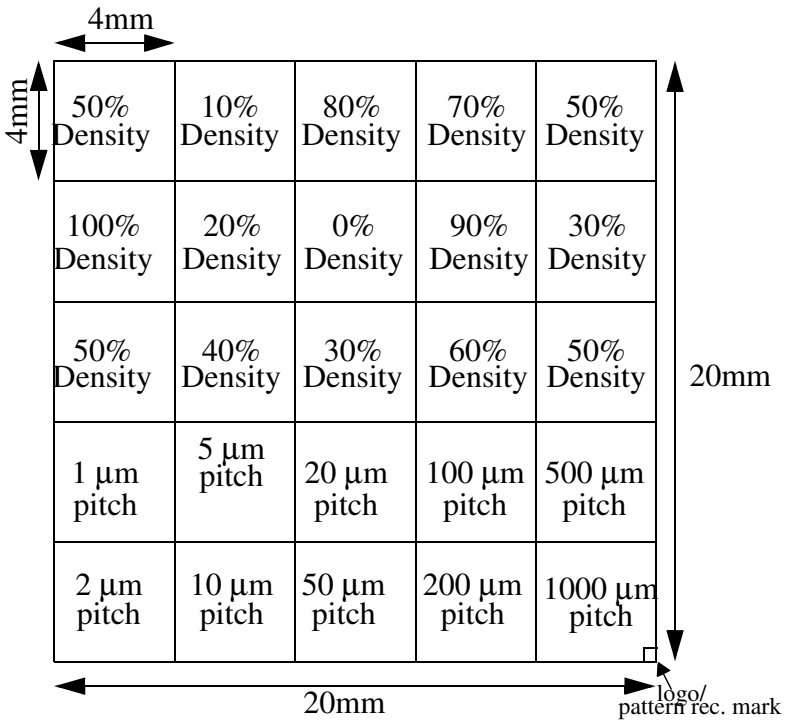
SKW Associates, Inc.

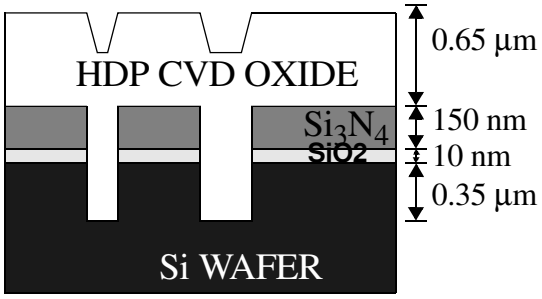
3370 Victor Court
Santa Clara, CA 95054
Phone: (408) 919-0094
Fax: (408) 919-0097
Email: skw@testwafer.com
http://www.testwafer.com

SKW3-764ETC303 300mm Wafer Specifications

DATE: December 09, 2005



SKW3-764ETC303 Mask Floor Plan



Cross Sectional View

PARAMETER	NOMINAL	TOLERANCE
Patterning		
Center Die X Location	-10.000 mm	+/- 100 µm
Center Die Y Location	-10.000 mm	+/- 100 µm
Die Size: X	20 mm	+/- 10 µm
Die Size: Y	20 mm	+/- 10 µm
Vertical Die Spacing	180 µm	+/- 10 %

Horizaontal Spacing	360 µm	+/- 10 %
Linewidth Variation (measured on 10 µm and 90 µm structures)		
Lot-to-Lot	10 µm, 90 µm	+/- 1 µm
Within-Lot (Wafer-to-Wafer)		+/- 1 µm
Within-Wafer		+/- 1 µm
Within-Die		+/- 1 µm
Raisde Area Thickness (HDP CVD Oxide Fill)		
Lot-to-Lot	0.65 µm	+/- 10 %
Within-Lot (Wafer-to-Wafer)		+/- 10 %
Within-Wafer		+/- 5 %
Within-Die		+/- 5 %
Raised Area Thickness (Nitride)		
Lot-to-Lot	1500 Å	+/- 10 %
Within-Lot (Wafer-to-Wafer)		+/- 10 %
Within-Wafer		+/- 5 %
Within-Die		+/- 5 %
Raised Area Thickness (Pad Oxide)		
Lot-to-Lot	100 Å	+/- 10 %
Within-Lot (Wafer-to-Wafer)		+/- 10 %
Within-Wafer		+/- 5 %
Within-Die		+/- 5 %
Silicon Trench Depth		
Lot-to-Lot	3500 Å	+/- 10 %
Within-Lot (Wafer-to-Wafer)		+/- 10 %
Within-Wafer		+/- 10 %
Within-Die		+/- 10 %